

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|---|------------------|---------|------------------|
| L2 | 1913 | 257/40.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 16:57 |
| L3 | 369 | 257/642.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 16:58 |
| L4 | 215 | 257/643.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 16:58 |
| L5 | 578 | 257/759.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 16:58 |
| L6 | 215 | 438/82.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 16:58 |
| L7 | 650 | 438/99.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 17:00 |
| L10 | 1036 | (gate near (insulat\$3 dielectric)) and organic and (crystal near growth) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 18:32 |
| L17 | 21232 | (gate near electrode) with (source near electrode) with (drain near electrode) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 18:33 |

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|-----|-----|--|--|----|----|------------------|
| L18 | 192 | 17 and 10 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 18:22 |
| L20 | 188 | (insulat\$3 dielectric) same organic same (crystal near growth) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2006/03/02 18:25 |
| L22 | 0 | semiconductor AND (current near channel) AND (gate near (oxide insulat\$3 dielectric)) AND organic AND (crystal near growth) AND (gate near electrode) AND (source near electrode) AND (drain near electrode) AND ((conduct\$3 metal\$3) near oxide). CLM. | US-PGPUB; USPAT | OR | ON | 2006/03/02 18:34 |